

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	2676	(257/306,758).CCLS.	USPAT; US-PGPUB	2003/03/26 09:03
2	BRS	882	((257/306,758).CCLS.) and @pd>20011221	USPAT; US-PGPUB	2003/03/26 09:22
3	IS&R	2	((("5061985") or ("5500558"))).PN.	USPAT; US-PGPUB	2003/03/26 09:23
4	IS&R	1	("6384441").PN.	USPAT; US-PGPUB	2003/03/26 09:24
5	BRS	13	("5237187" "5847428" "5899721" "6033981" "6040223" "6150689" "6153455" "6153476" "6165826" "6198144" "6278152" "6319779" "6344692").PN.	USPAT	2003/03/26 12:57
6	IS&R	1	("5,710,450").PN.	USPAT; US-PGPUB	2003/03/26 14:17
7	IS&R	1	("6200858").PN.	USPAT; US-PGPUB	2003/03/26 14:19
8	BRS	6	("5729035" "5830794" "5879992" "5879993" "5960285" "5962891").PN.	USPAT	2003/03/26 14:17
9	BRS	424	ono same dram	USPAT; US-PGPUB	2003/03/26 14:21
10	BRS	118	(ono same dram) same gate	USPAT; US-PGPUB	2003/03/26 14:20
11	BRS	22	(ono with gate) same dram	USPAT; US-PGPUB	2003/03/26 14:23
12	BRS	2	(ono with sidewall) same dram	USPAT; US-PGPUB	2003/03/26 14:32
13	BRS	82	((silicon adj nitride) with sidewall) same dram	USPAT; US-PGPUB	2003/03/26 14:33

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1470	lee.in. and dram	USPAT; US-PGPUB	2003/03/26 15:04
2	BRS	L2	128	lee.in. and dram and park.in.	USPAT; US-PGPUB	2003/03/26 15:03
3	BRS	L3	3	2 and giga adj bit	USPAT; US-PGPUB	2003/03/26 15:03
4	BRS	L4	149	lee-k\$.in. and dram	USPAT; US-PGPUB	2003/03/26 15:04

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 20020030209 A1	49	SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME	257/296	257/306	Sugiyama, Koichi et al.
2	US 6501114 B2	14	Structures comprising transistor gates	257/296	257/300; 257/306; 438/241; 438/303; 438/305	Cho, Chih-Chen et al.
3	US 6344692 B1	51	Highly integrated and reliable DRAM adapted for self-aligned contact	257/758	257/296; 438/622; 438/791	Ikemasu, Shinichiroh et al.
4	US 6333548 B1	19	Semiconductor device with etch stopping film	257/652	257/758; 257/773	Yamane, Tomoko et al.
5	US 5061985 A	15	Semiconductor integrated circuit device and process for producing the same	257/751	257/754; 257/758; 257/761; 257/764; 257/765	Meguro, Hideo et al.
6	US 5500558 A	28	Semiconductor device having a planarized surface	257/758	257/760	Hayashide, Yoshio
7	US 6384441 B1	46	Semiconductor device and method of manufacturing the same	257/296	257/300; 257/774	Sugiyama, Koichi et al.